

E4M0025075K1

Silicon Carbide Power MOSFET
E-Series Automotive
N-Channel Enhancement Mode



Features

- Optimized package with separate driver source pin
- High blocking voltage with low on-resistance
- High-speed switching with low capacitances
- Fast intrinsic diode with low reverse recovery (Q_{rr})
- Halogen free, RoHS compliant
- Automotive Qualified (AEC-Q101) and PPAP Capable

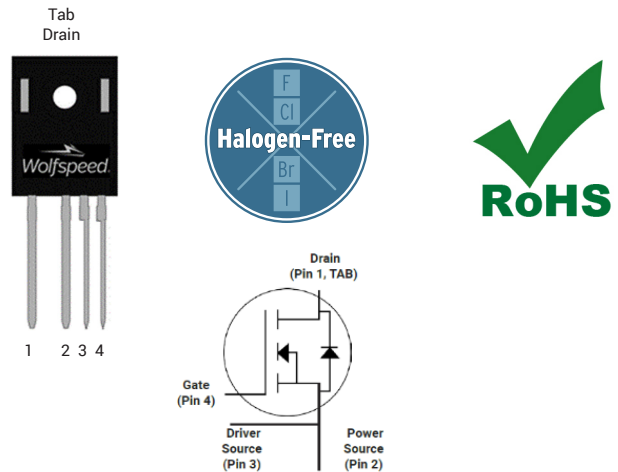
Benefits

- Reduce switching losses and minimize gate ringing
- Higher system efficiency
- Reduce cooling requirements
- Increase power density
- Increase system switching frequency

Applications

- Motor Control
- EV Battery Chargers
- High Voltage DC/DC Converters

Package



Part Number	Package	Marking
E4M0025075K1	TO-247-4L	E4M0025075K1

Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Note
V_{DSmax}	Drain - Source Voltage	750	V	
V_{GSmax}	Gate - Source Voltage	-8/+19	V	Note: 1
I_D	Continuous Drain Current, $V_{GS} = 15\text{ V}$	$T_c = 25^\circ\text{C}$	80	A Fig. 19 Note: 2
		$T_c = 100^\circ\text{C}$	59	
$I_{D(pulse)}$	Pulsed Drain Current, Pulse width t_p limited by T_{jmax}	251	A	Fig. 22
P_D	Power Dissipation, $T_c=25^\circ\text{C}$, $T_j = 175^\circ\text{C}$	262	W	Fig. 20 Note: 2
T_j, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$	
T_L	Solder Temperature, 1.6mm (0.063") from case for 10s	260	$^\circ\text{C}$	
M_d	Mounting Torque, M3 or 6-32 screw	1	Nm	
		8.8	lbf-in	

Note (1): Recommended turn off / turn on gate voltage $V_{GS} = -4V..0V / +15V$

Note (2): Verified by design


Electrical Characteristics ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	750			V	$V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$	
$V_{GS(th)}$	Gate Threshold Voltage	1.8	2.6	3.8	V	$V_{DS} = V_{GS}, I_D = 9.22\text{ mA}$	Fig. 11
			2.1		V	$V_{DS} = V_{GS}, I_D = 9.22\text{ mA}, T_J = 175^\circ\text{C}$	
I_{DSS}	Zero Gate Voltage Drain Current		1	50	μA	$V_{DS} = 750\text{ V}, V_{GS} = 0\text{ V}$	
I_{GSS}	Gate-Source Leakage Current		10	250	nA	$V_{GS} = 15\text{ V}, V_{DS} = 0\text{ V}$	
$R_{DS(on)}$	Drain-Source On-State Resistance		25	34	m Ω	$V_{GS} = 15\text{ V}, I_D = 33.5\text{ A}$	Fig. 4, 5, 6
			35			$V_{GS} = 15\text{ V}, I_D = 33.5\text{ A}, T_J = 175^\circ\text{C}$	
g_{fs}	Transconductance		24		S	$V_{DS} = 20\text{ V}, I_{DS} = 33.5\text{ A}$	Fig. 7
			18			$V_{DS} = 20\text{ V}, I_{DS} = 33.5\text{ A}, T_J = 175^\circ\text{C}$	
C_{iss}	Input Capacitance		3055		pF	$V_{GS} = 0\text{ V}, V_{DS} = 0\text{ V to } 500\text{ V}$ $F = 100\text{ kHz}$ $V_{AC} = 25\text{ mV}$	Fig. 17, 18
C_{oss}	Output Capacitance		158				
C_{rss}	Reverse Transfer Capacitance		16				
E_{oss}	C_{oss} Stored Energy		23		μJ		Fig. 16
$C_{o(er)}$	Effective Output Capacitance (Energy Related)		201		pF	$V_{GS} = 0\text{ V}, V_{DS} = 0 \dots 500\text{ V}$	Note: 3
$C_{o(tr)}$	Effective Output Capacitance (Time Related)		291		pF		
E_{ON}	Turn-On Switching Energy (External Diode)		144		μJ	$V_{DS} = 500\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}, I_D = 33.5\text{ A},$ $R_{G(ext)} = 2.5\text{ }\Omega, L = 59\text{ }\mu\text{H}, T_J = 175^\circ\text{C}$ FWD = External SiC DIODE	Fig. 26, 28
E_{OFF}	Turn Off Switching Energy (External Diode)		103				
E_{ON}	Turn-On Switching Energy (Body Diode FWD)		224		μJ	$V_{DS} = 500\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}, I_D = 33.5\text{ A},$ $R_{G(ext)} = 2.5\text{ }\Omega, L = 59\text{ }\mu\text{H}, T_J = 175^\circ\text{C}$ FWD = Internal Body Diode	Fig. 26, 28
E_{OFF}	Turn-Off Switching Energy (Body Diode FWD)		92				
$t_{d(on)}$	Turn-On Delay Time		12		ns	$V_{DD} = 500\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}$ $I_D = 33.5\text{ A}, R_{G(ext)} = 2.5\text{ }\Omega,$ Timing relative to V_{DS} Inductive load	Fig. 27, 28
t_r	Rise Time		18				
$t_{d(off)}$	Turn-Off Delay Time		31				
t_f	Fall Time		10				
$R_{G(int)}$	Internal Gate Resistance		2.0		Ω	$f = 1\text{ MHz}, V_{AC} = 25\text{ mV}$	
Q_{gs}	Gate to Source Charge		33		nC	$V_{DS} = 500\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}$ $I_D = 33.5\text{ A}$ Per IEC60747-8-4 pg 21	Fig. 12
Q_{gd}	Gate to Drain Charge		40				
Q_g	Total Gate Charge		119				

Note (3): $C_{o(er)}$, a lumped capacitance that gives same stored energy as C_{oss} while V_{ds} is rising from 0 to 500V

$C_{o(tr)}$, a lumped capacitance that gives same charging time as C_{oss} while V_{ds} is rising from 0 to 500V

Reverse Diode Characteristics (T_c = 25°C unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V _{SD}	Diode Forward Voltage	4.8		V	V _{GS} = -4 V, I _{SD} = 16.8 A, T _J = 25 °C	Fig. 8, 9, 10
		4.2		V	V _{GS} = -4 V, I _{SD} = 16.8 A, T _J = 175 °C	
I _S	Continuous Diode Forward Current		47	A	V _{GS} = -4 V, T _c = 25°C	
I _{S, pulse}	Diode pulse Current		251	A	V _{GS} = -4 V, pulse width t _p limited by T _{Jmax}	
t _{rr}	Reverse Recover time	29		ns	V _{GS} = -4 V, I _{SD} = 33.5 A, V _R = 500 V dif/dt = 2185 A/μs, T _J = 175 °C	
Q _{rr}	Reverse Recovery Charge	372		nC		
I _{rrm}	Peak Reverse Recovery Current	23		A		
t _{rr}	Reverse Recover time	20		ns	V _{GS} = -4 V, I _{SD} = 33.5 A, V _R = 500 V dif/dt = 6235 A/μs, T _J = 175 °C	
Q _{rr}	Reverse Recovery Charge	601		nC		
I _{rrm}	Peak Reverse Recovery Current	52		A		

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
R _{θJC}	Thermal Resistance from Junction to Case	0.45	0.57	°C/W		Fig. 21



Typical Performance

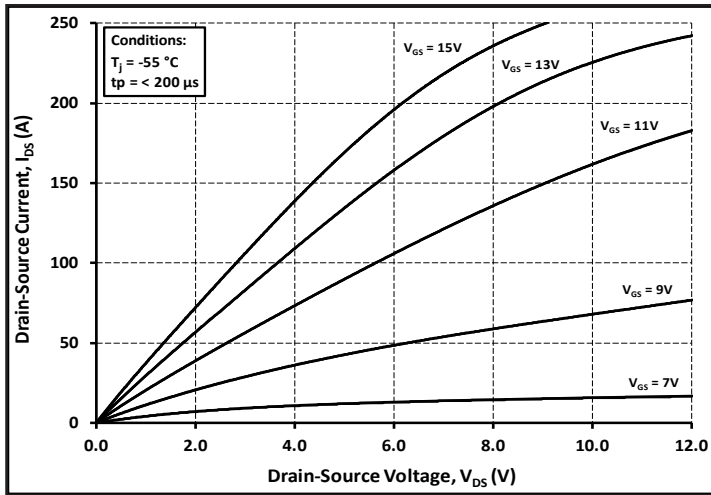


Figure 1. Output Characteristics $T_J = -55\text{ }^{\circ}\text{C}$

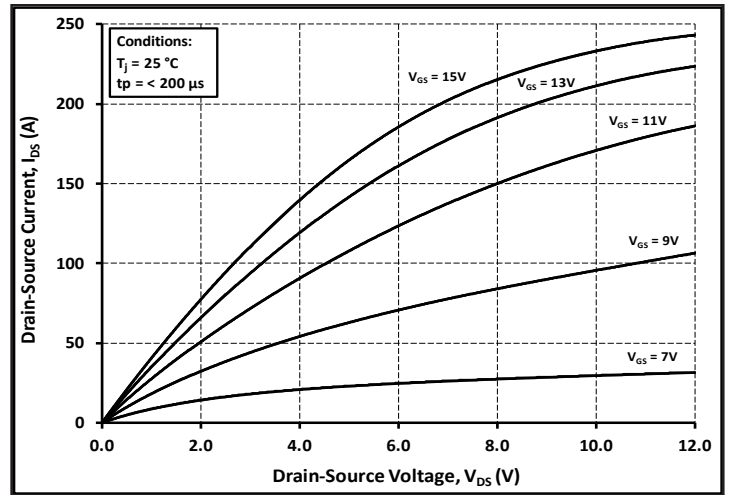


Figure 2. Output Characteristics $T_J = 25\text{ }^{\circ}\text{C}$

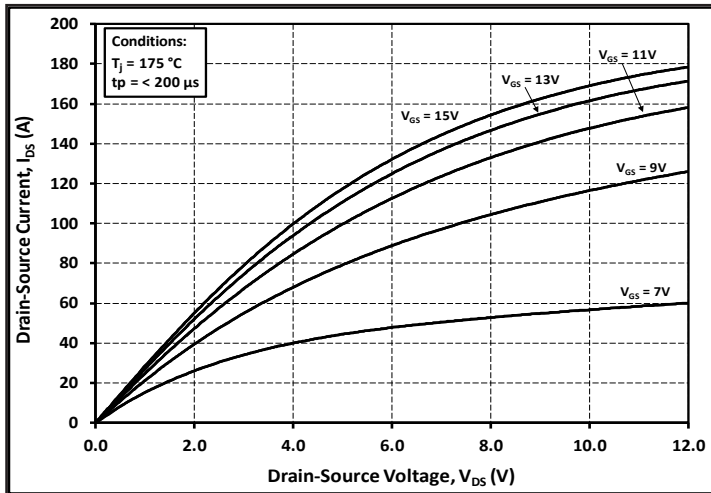


Figure 3. Output Characteristics $T_J = 175\text{ }^{\circ}\text{C}$

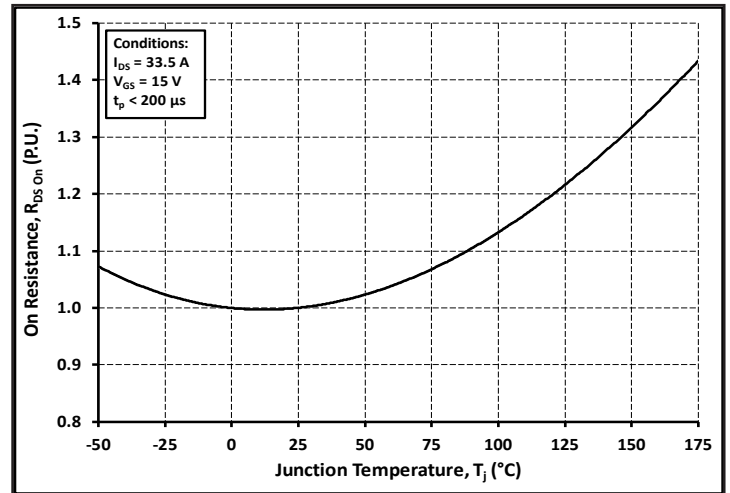


Figure 4. Normalized On-Resistance vs. Temperature

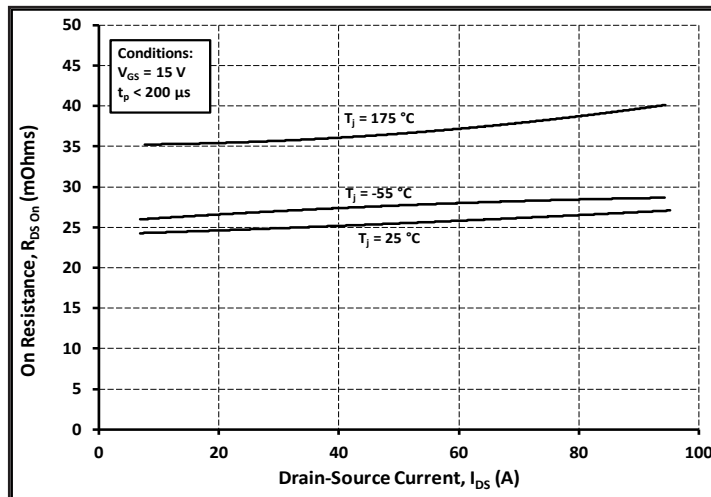


Figure 5. On-Resistance vs. Drain Current For Various Temperatures

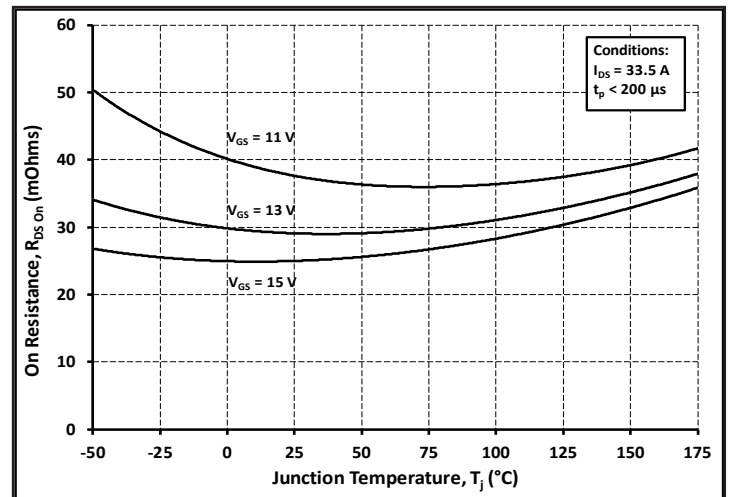


Figure 6. On-Resistance vs. Temperature For Various Gate Voltage

Typical Performance

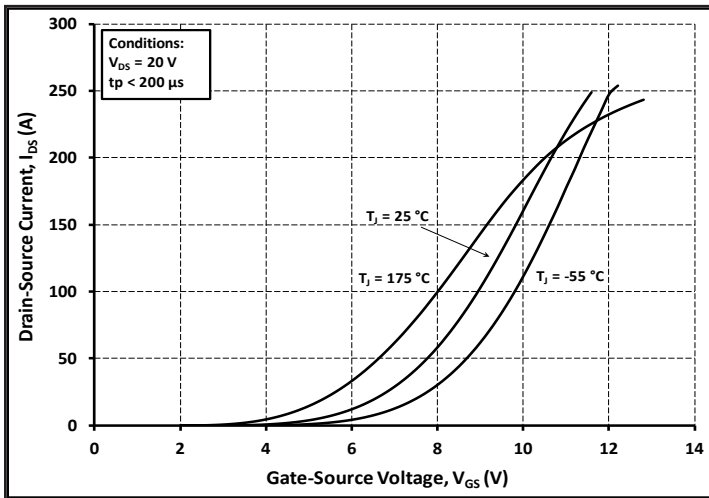


Figure 7. Transfer Characteristic for Various Junction Temperatures

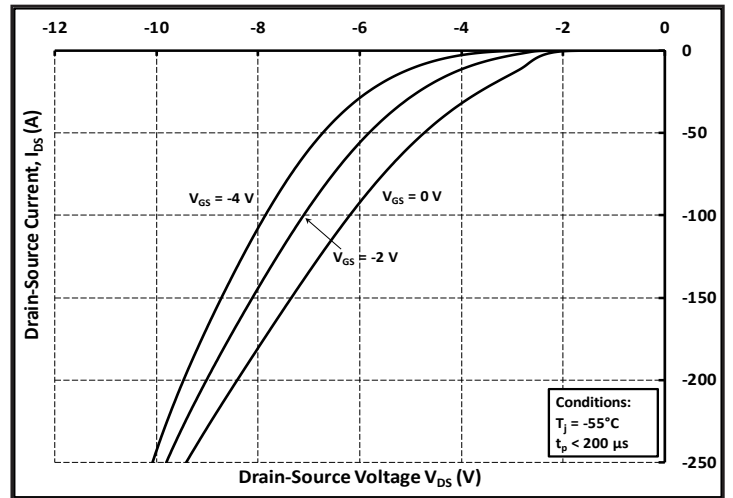


Figure 8. Body Diode Characteristic at -55°C

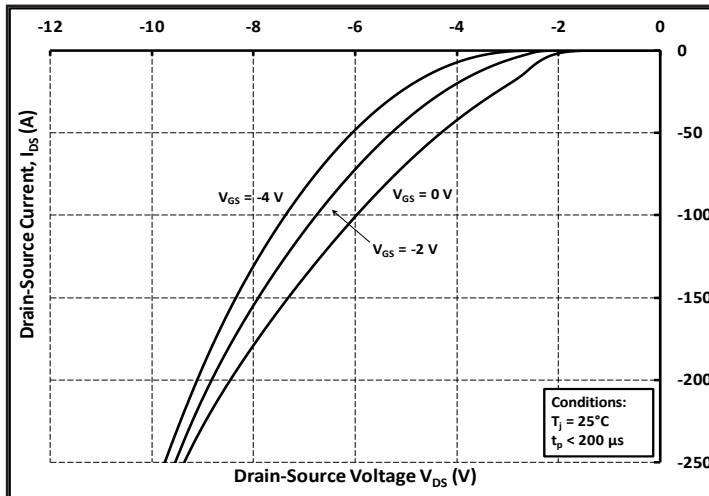


Figure 9. Body Diode Characteristic at 25°C

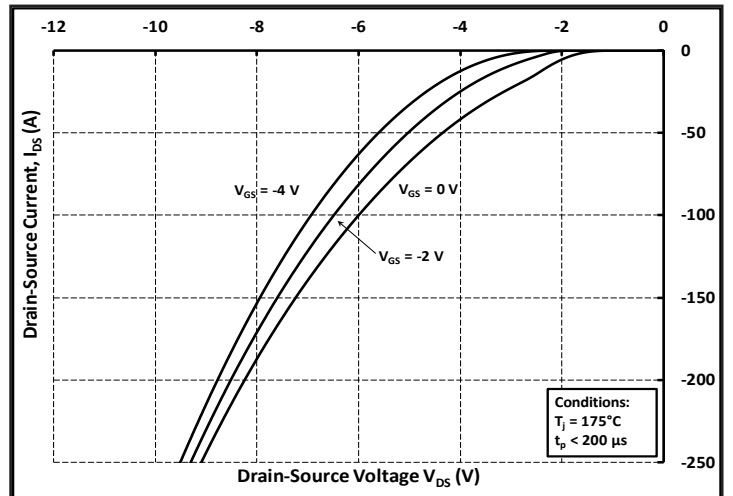


Figure 10. Body Diode Characteristic at 175°C

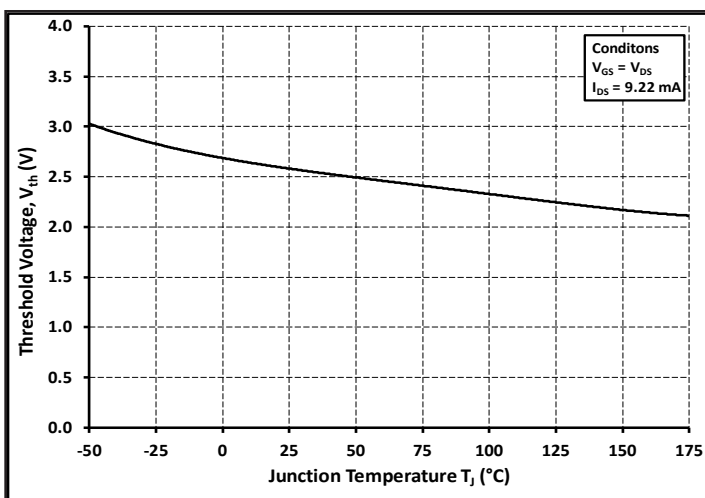


Figure 11. Threshold Voltage vs. Temperature

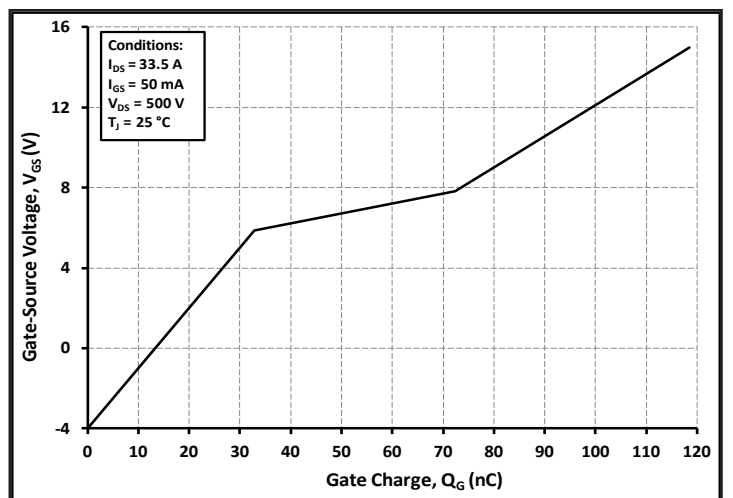


Figure 12. Gate Charge Characteristics

Typical Performance

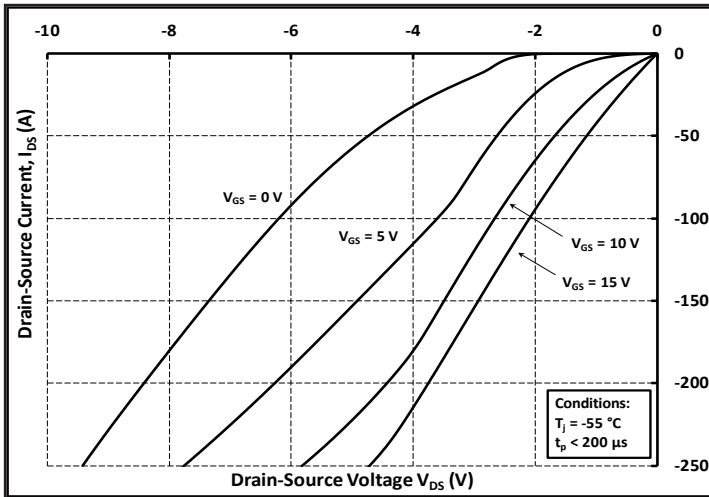
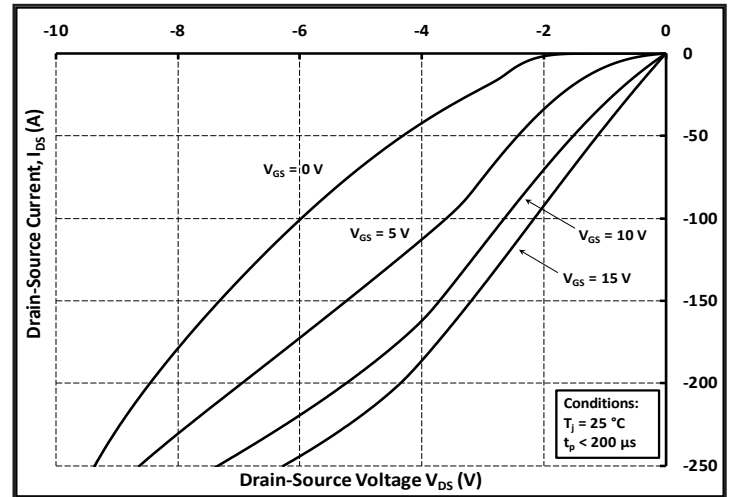
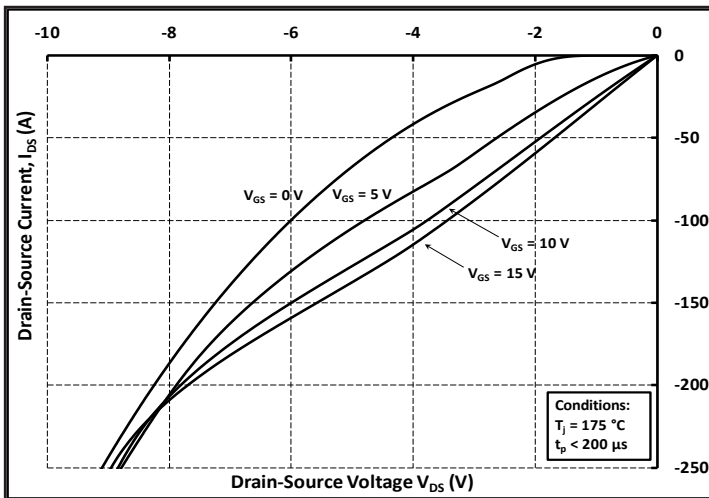
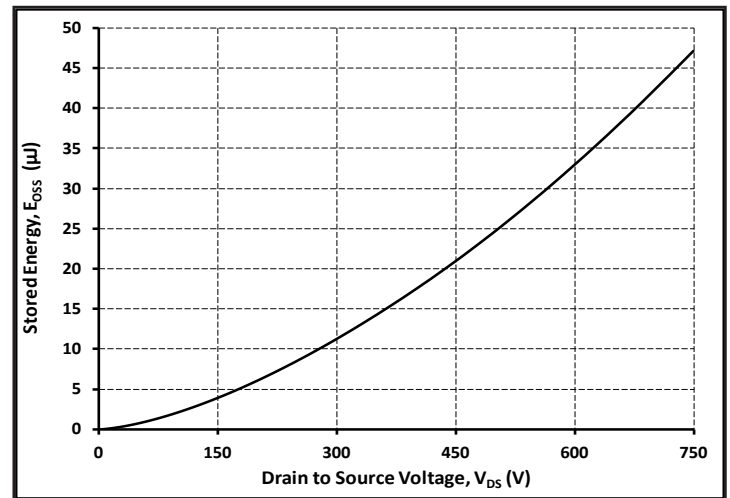
Figure 13. 3rd Quadrant Characteristic at $-55\text{ }^{\circ}\text{C}$ Figure 14. 3rd Quadrant Characteristic at $25\text{ }^{\circ}\text{C}$ Figure 15. 3rd Quadrant Characteristic at $175\text{ }^{\circ}\text{C}$ 

Figure 16. Output Capacitor Stored Energy

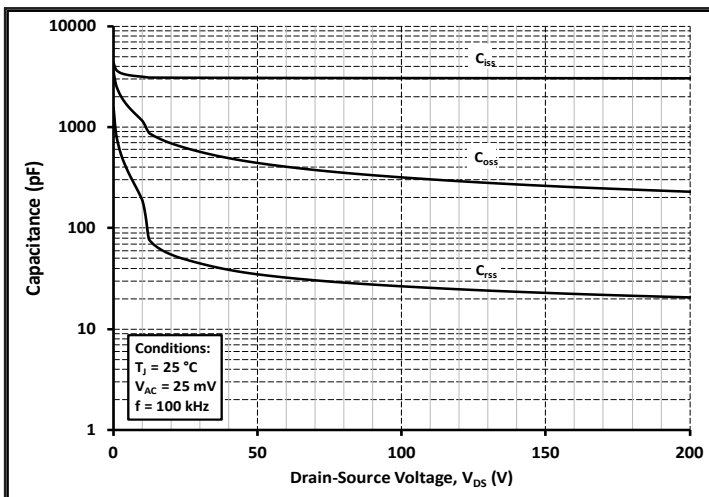


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

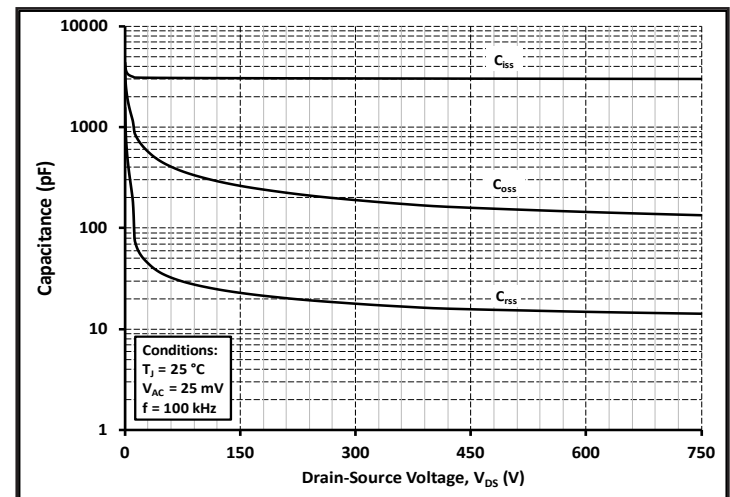


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 750V)

Typical Performance

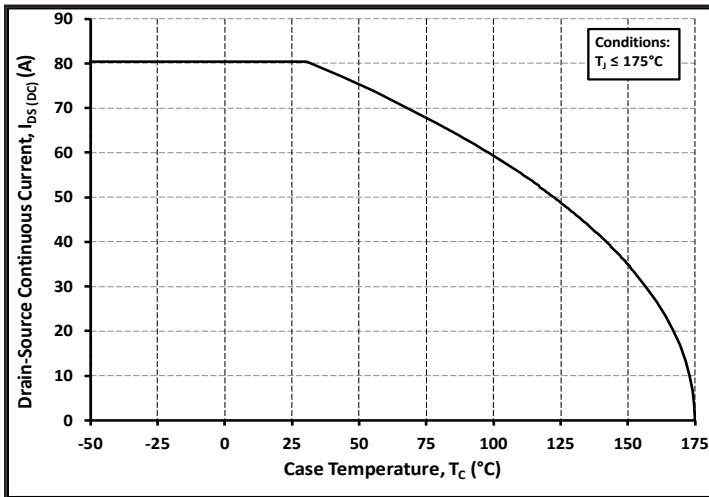


Figure 19. Continuous Drain Current Derating vs. Case Temperature

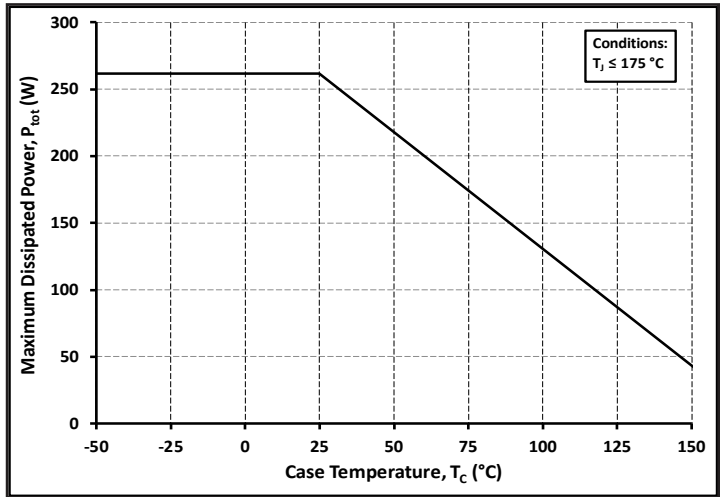


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

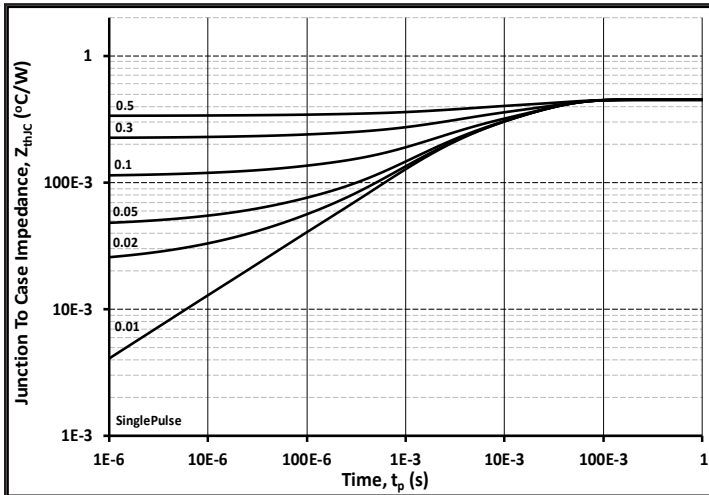


Figure 21. Transient Thermal Impedance (Junction - Case)

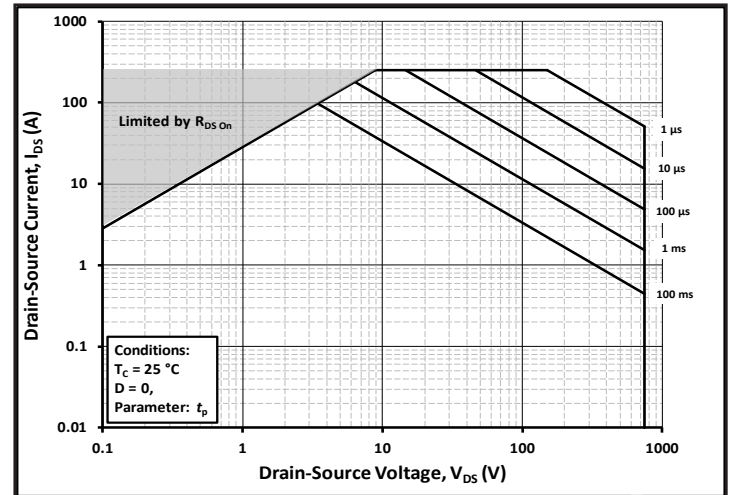
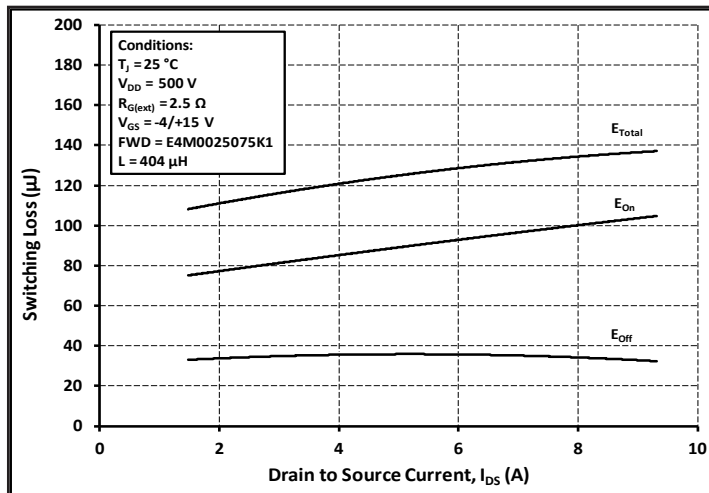
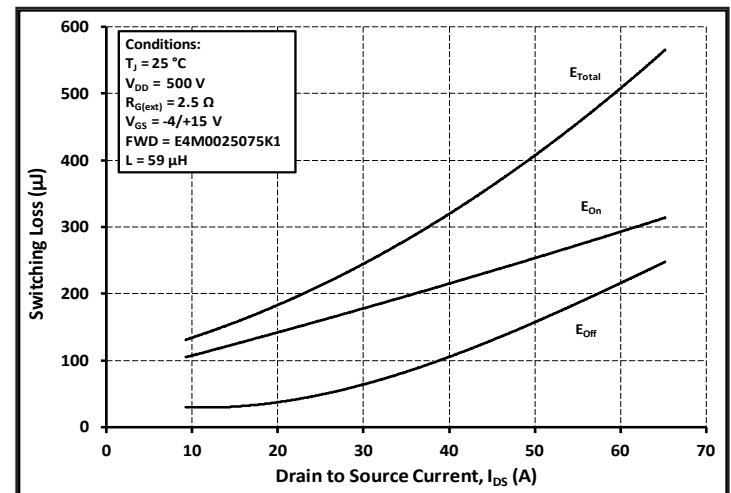


Figure 22. Safe Operating Area

Figure 23. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 500V$)Figure 24. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 500V$)

Typical Performance

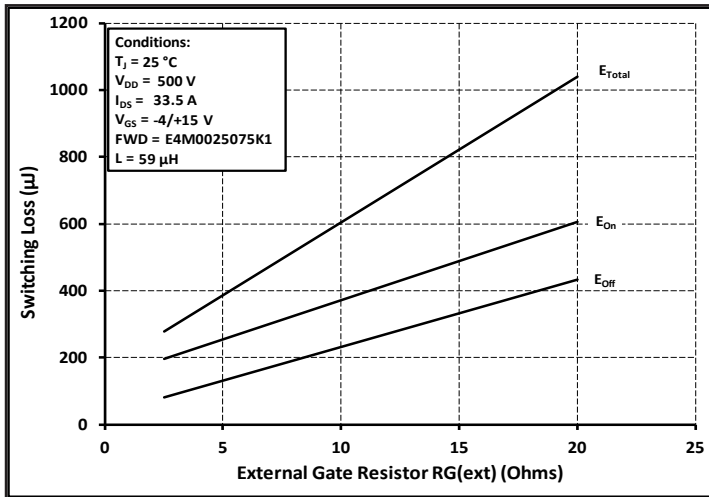
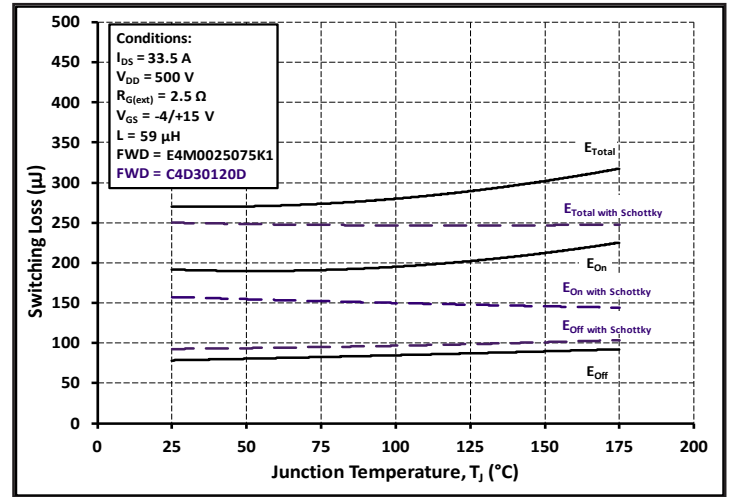
Figure 25. Clamped Inductive Switching Energy vs. $R_{G(\text{ext})}$ 

Figure 26. Clamped Inductive Switching Energy vs. Temperature

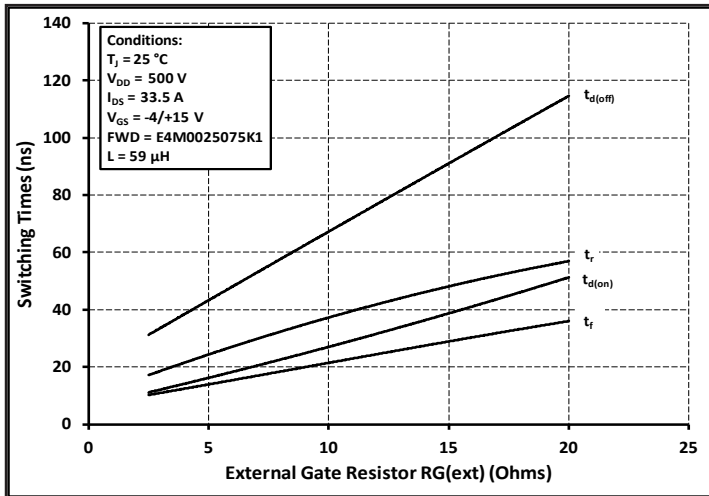
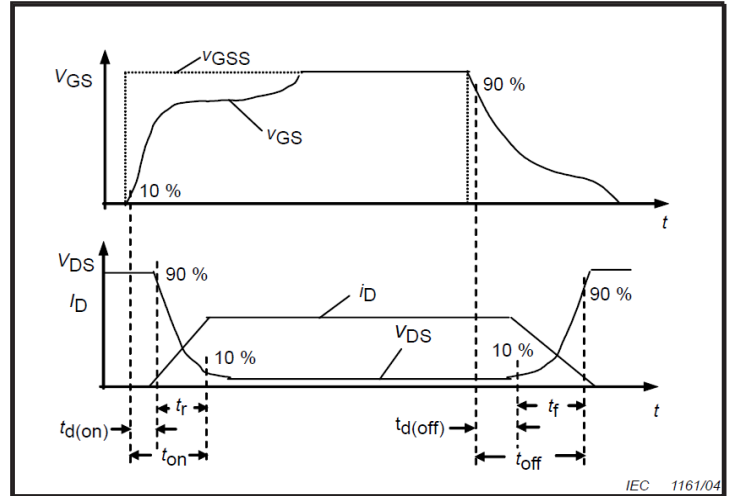
Figure 27. Switching Times vs. $R_{G(\text{ext})}$ 

Figure 28. Switching Times Definition

Test Circuit Schematic

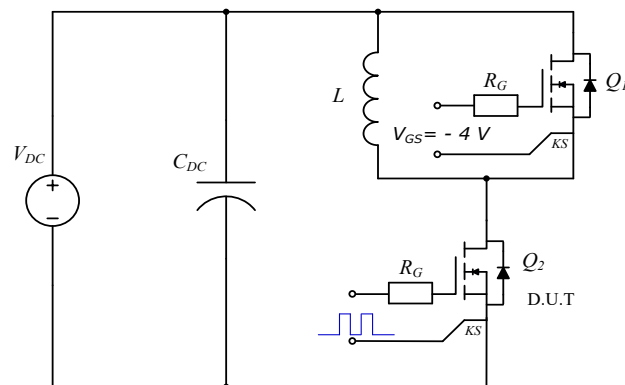
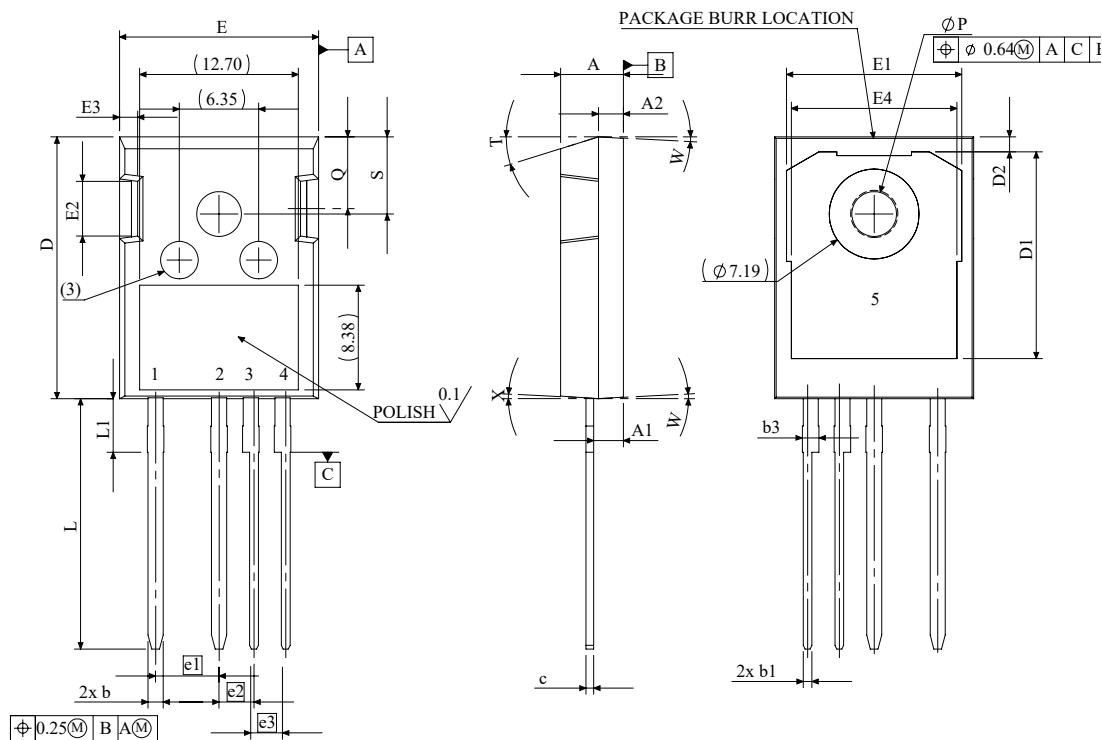


Figure 29. Clamped Inductive Switching
Waveform Test Circuit

Package Dimensions



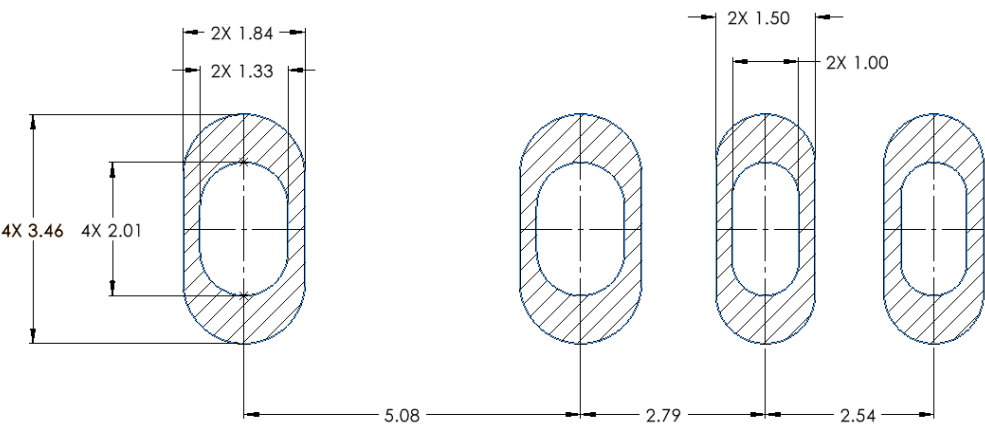
SYMBOL	MIN (mm)	MAX (mm)
A	4.83	5.21
A1	2.22	2.6
A2	1.91	2.16
b	1.10	1.30
b1	0.65	0.79
b3	1.34	1.44
c	0.55	0.68
D	20.76	21.14
D1	16.25	17.65
D2	0.92	1.42
E	15.75	16.13
E1	13.1	14.15
E2	3.68	5.10
E3	1.00	1.90
E4	12.38	13.43
e1	5.08 BSC	
e2	2.79 BSC	
e3	2.54 BSC	
L	19.72	20.32
L1	3.87	4.47
ØP	3.51	3.65
Q	5.49	6.00
S	6.04	6.30
T	17.5° REF.	
W	3.5° REF.	
X	4° REF.	

1	DRAIN
2	SOURCE
3	SOURCE
4	GATE
5	DRAIN

- NOTE:
1. ALL METAL SURFACES ARE TIN PLATED (MATTE), EXCEPT AREA OF CUT.
 2. DIMENSIONING & TOLERANCING CONFORM TO ASME Y14.5M-1994.
 3. ALL DIMENSIONS ARE LISTED IN MILLIMETERS. ANGLES ARE IN DEGREES.
 4. BURR OR MOLD FLASH SIZE (0.5 mm) IS NOT INCLUDED IN THE DIMENSIONS

Recommended Solder Pad Layout

All dimensions in mm



Revision history

Document Version	Date of release	Descriptiion of changes
1.0	January-2024	Initial datasheet



Notes & Disclaimer

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